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The *Journal of Electronic Materials* provides a common forum for rapid dissemination of the results of original research on all materials of interest in the field of electronics. Representative fields of activity for which manuscripts are invited include materials for memory, logic, display, interconnections, packaging, detectors, emitters, large stores, and hard copy. In addition, general papers relating to the processing of electronic materials for device applications, structure making, reliability and yield, etc., are welcome.

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